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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known				
Application Number	10/616,492			
Filing Date	07/08/2003			
First Named Inventor	Yao-Sheng Lee			
Art Unit	1763			
Examiner Name				
Attorney Docket Number	074361.00015			

			U. S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (f known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
BV		<sup>US-</sup> 6,350,390	02-26-2002	Liu et al.	
1		<sup>US-</sup> 6,514,378	02-04-2003	Ni et al.	
		<sup>US-</sup> 5,545,290	08-13-1996	Douglas	
		<sup>US-</sup> 2002/0037647	03-28-2002	Hwang et al.	
		<sup>US-</sup> 2003/0059720	03-27-2003	Hwang et al.	
		<sup>US-</sup> 6,323,132	11-27-2001	Hwang et al.	
		<sup>US-</sup> 5,419,804	05-30-1995	Ojha et al.	
		<sup>US-</sup> 5,869,398	02-09-1999	Knight	
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Initials* No.1  Country Code3 Number 4 Kind Code3 (if known)		Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	
	MM-DD-YYYY	Applicant of Orico Document	Or Relevant Figures Appear	7⁴		
134	L	JP 09050983	02-18-1997	Fujitsu Ltd.	,	
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MI		JP 403141640	06-17-1991	Tatsumi, Tetsuya		

Examiner Signature	B. L. Train	Date	FLICIAL
Signature	_ SINN TOOL	Considered	3143103

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. Senter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached.

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AM				Application Number	10/616,492	
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STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Yao-Sheng Lee	
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	(Ose as many si	icora da l	recessary)	Examiner Name		
Sheet	2	of	2	Attorney Docket Number	074361.00015	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
131		S. OKU, Y. SHIBATA, and K. OCHIAI, "Controlled Beam Dry Etching of InP by Using Br2-N2 Gas," J. Electron Mater., Vol 25, pp. 585-591,1996.	
		D.J. THOMAS K. POWELL, M.M. BOURKE, Y.P. SONG and C. FRAGOS, "High Density Plasma Etch Processes for the Manufacture of Optoelectronic Devices based on InP", GaAs MANTECH Digest of Papers - 2001, pp 172-174	4
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		S. AGARWALA, K. NUMMILA, H., I. ADESIDA, C. CANEAU, AND R. BHAT, "InAlAs/InGaAs Heterostructure FET's Processed with Selective Reactive-lon Etching Gate-Recess Technology" IEEE Electron Device Letters, Vol. 14, No. 9 pp 425-427 Sept. 93	
135		K. SHINODA, A. TAIKE, H.SATO, AND H. UCHIYAMA, "Highly Reliable InGaAsP/InP Lasers with Defect-Free Regrowth Interfaces Formed by Newly Composed HBr-Based Solutions" 2001 International Conference on Indium Phosphide and Hellated Mat. pp 409—412 May2	001

Examiner Signature	Binh Tran	Date Considered	5/25/05	
*EVAMINED: Initial if reference applicant whether a referring in the SECTION CO. D				

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